

Docket No.: R2184.0282/P282
(PATENT)

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of:
Hirokazu Iwata et al.

Application No.: Not Yet Assigned

Confirmation No.:

Filed: Concurrently Herewith

Art Unit: N/A

For: METHOD OF GROWING GROUP III
NITRIDE CRYSTAL, GROUP III NITRIDE
CRYSTAL GROWN THEREBY, GROUP III
NITRIDE CRYSTAL GROWING
APPARATUS AND SEMICONDUCTOR
DEVICE

Examiner: Not Yet Assigned

CLAIM FOR PRIORITY

MS Patent Application
Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Dear Sir:

Applicant hereby claims priority under 35 U.S.C. 119 based on the following
prior foreign applications filed in the following foreign countries on the dates indicated:

<u>Country</u>	<u>Application No.</u>	<u>Date</u>
Japan	2003-019716	January 29, 2003
Japan	2003-071302	March 17, 2003
Japan	2003-081836	March 25, 2003
Japan	2004-011536	January 20, 2004
Japan	2004-012906	January 21, 2004
Japan	2004-013562	January 21, 2004

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In support of this claim, a certified copy of each said original foreign application will be filed shortly.

Dated: January 28, 2004

Respectfully submitted,

By 

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